

Schottky barrier diode

RB451F

●Applications

Low power rectification

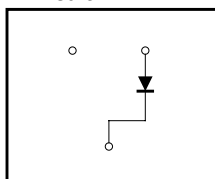
●Features

- 1) Small surface mounting type. (UMD3)
- 2) Low V_F . ($V_F=0.45V$ Typ. at 100mA)
- 3) High reliability.

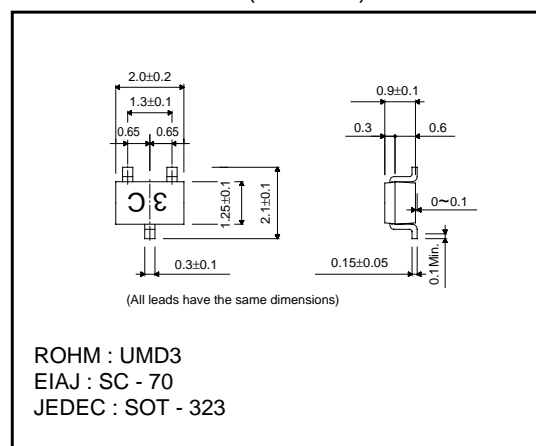
●Construction

Silicon epitaxial planar

●Circuit



●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	0.1	A
Peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+125	°C

* 60Hz for 1 \varnothing

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_{F1}	–	–	0.55	V	$I_F=100mA$
	V_{F2}	–	–	0.34	V	$I_F=10mA$
Reverse current	I_R	–	–	30	μA	$V_R=10V$
Capacitance between terminals	C_T	–	6.0	–	pF	$V_R=10V, f=1MHz$

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta = 25°C)

